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2SB892/2SD1207

Large-Current Switching Applications

Features

- Power supplies, relay drivers, lamp drivers, and automotive wiring.

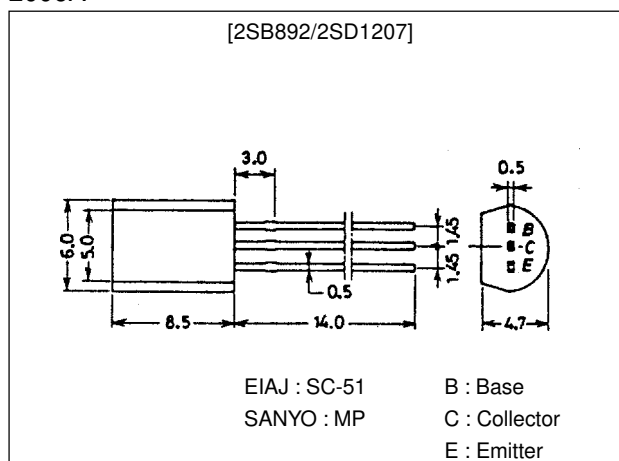
Features

- FBET and MBIT processed (Original process of SANYO).
- Low saturation voltage.
- Large current capacity and wide ASO.

Package Dimensions

unit:mm

2006A



() : 2SB892

Specifications

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		(-)60	V
Collector-to-Emitter Voltage	V_{CEO}		(-)50	V
Emitter-to-Base Voltage	V_{EBO}		(-)6	V
Collector Current	I_C		(-)2	A
Collector Current (Pulse)	I_{CP}		(-)4	A
Allowable Collector Dissipation	P_C		1	W
Junction Temperature	T_J		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$

Electrical Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB}=(-)50\text{V}, I_E=0$			(-)0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=(-)4\text{V}, I_C=0$			(-)0.1	μA
DC Current Gain	h_{FE1}	$V_{CE}=(-)2\text{V}, I_C=(-)100\text{mA}$	100		560	
	h_{FE2}	$V_{CE}=(-)2\text{V}, I_C=(-)1.5\text{A}$	40			
Gain-Bandwidth Product	f_T	$V_{CE}=(-)10\text{V}, I_C=(-)50\text{mA}$		150		MHz
Output Capacitance	C_{ob}	$V_{CB}=(-)10\text{V}, f=1\text{MHz}$		12		pF
				(22)		pF

* : The 2SB892/2SD1207 are graded as follows by h_{FE} at 100mA :

100	R	200	140	S	280	200	T	400	280	U	560
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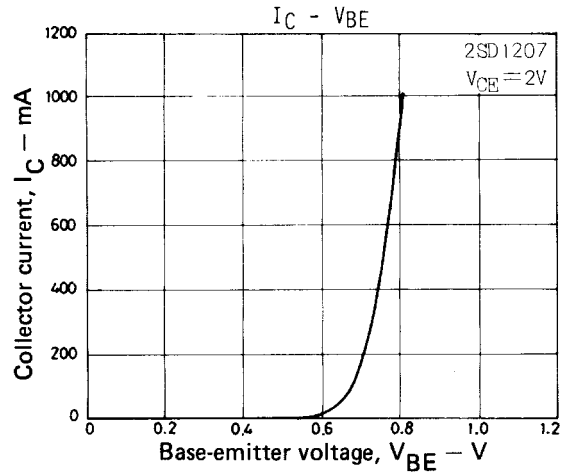
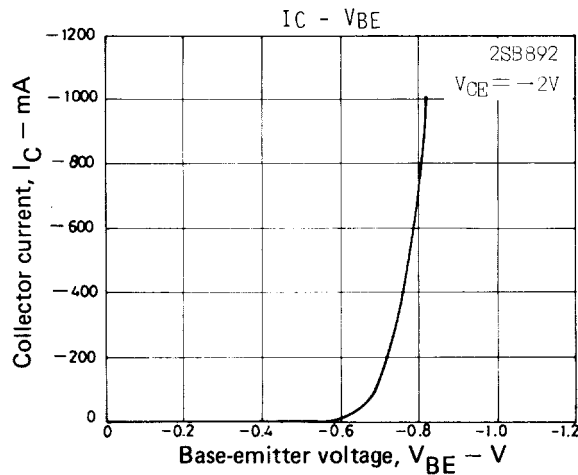
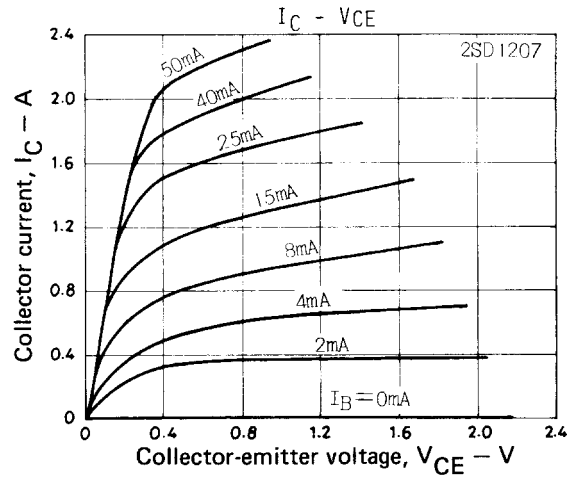
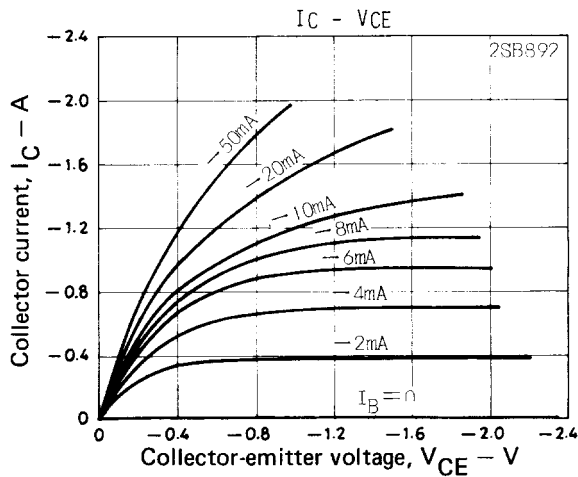
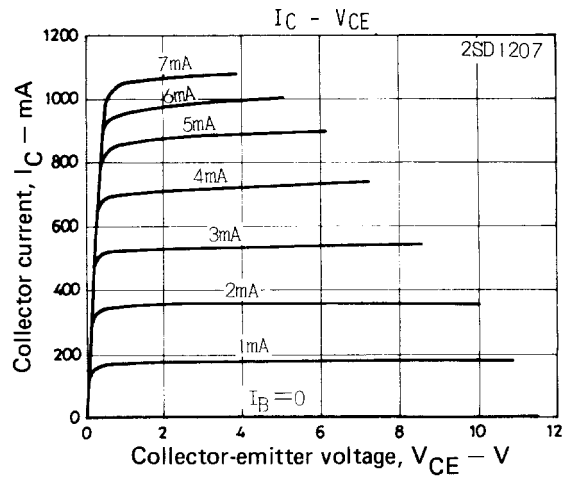
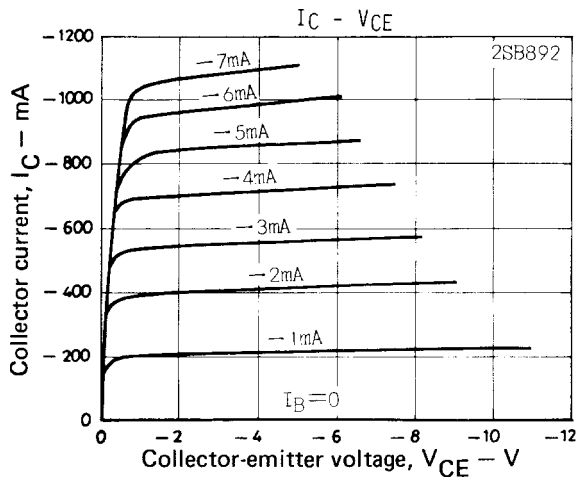
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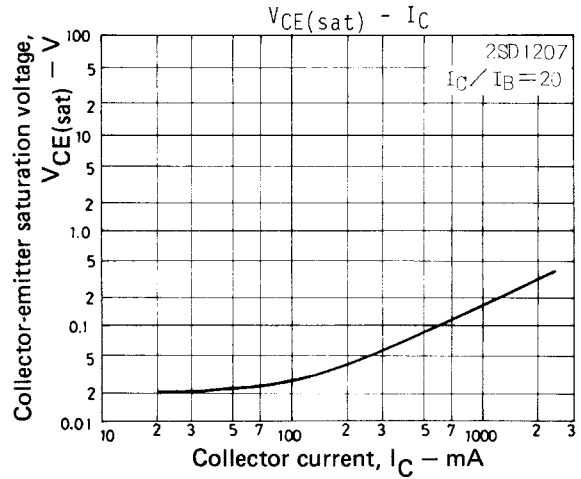
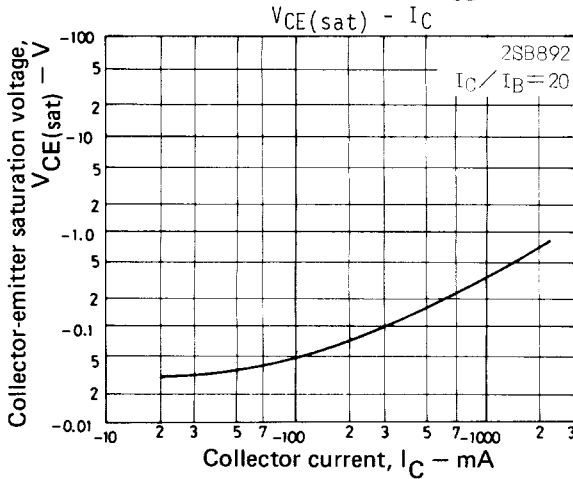
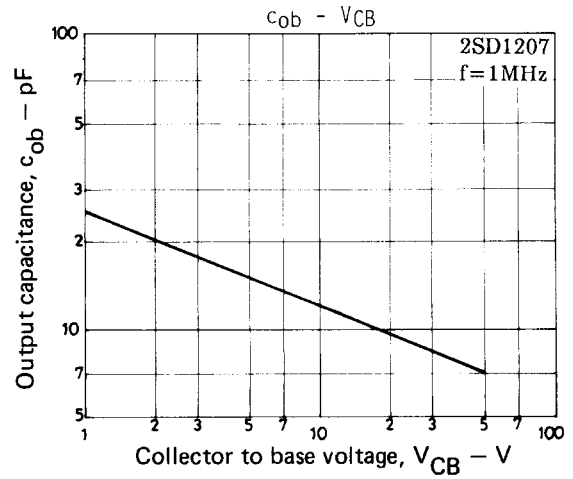
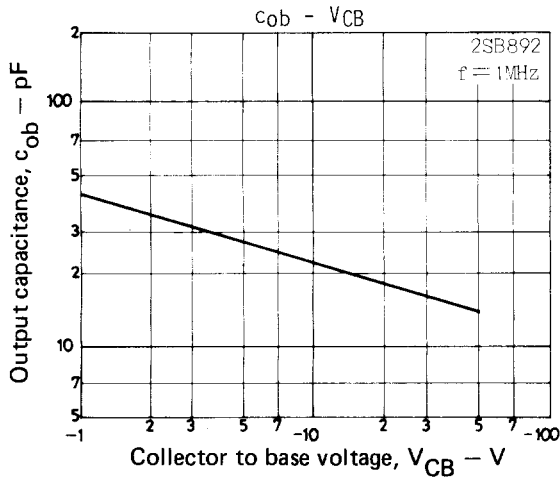
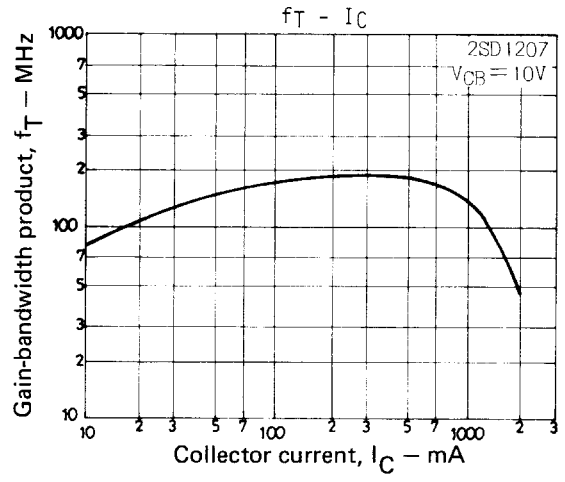
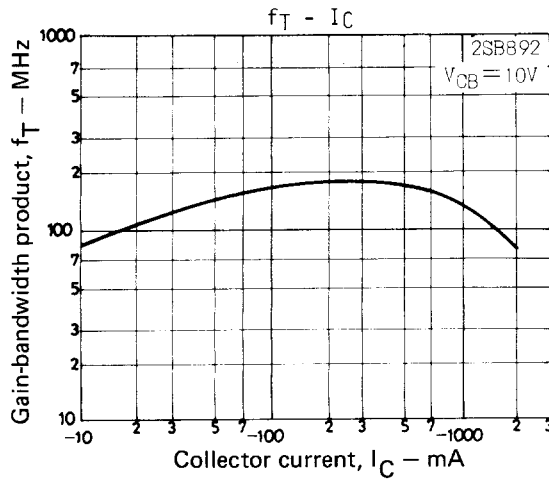
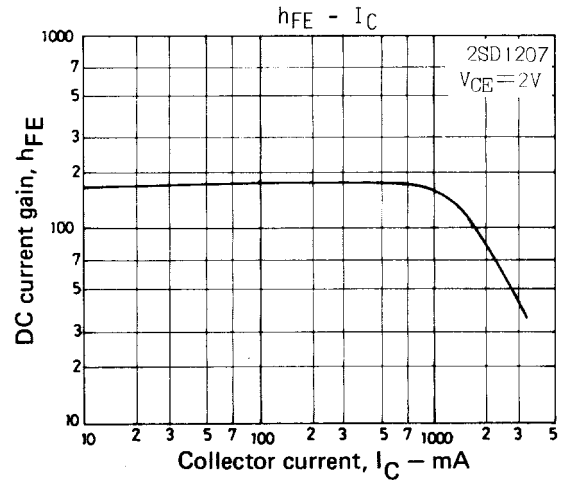
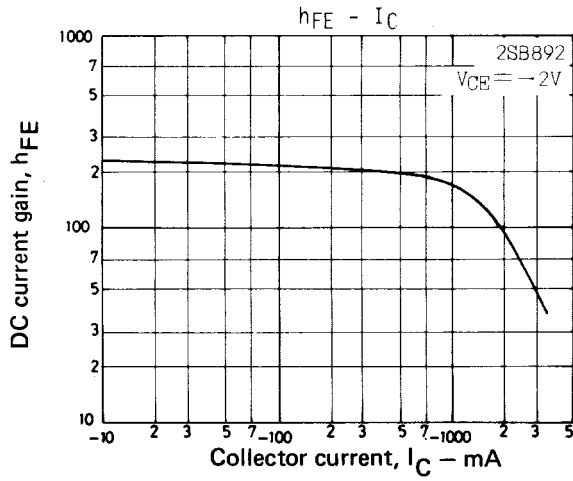
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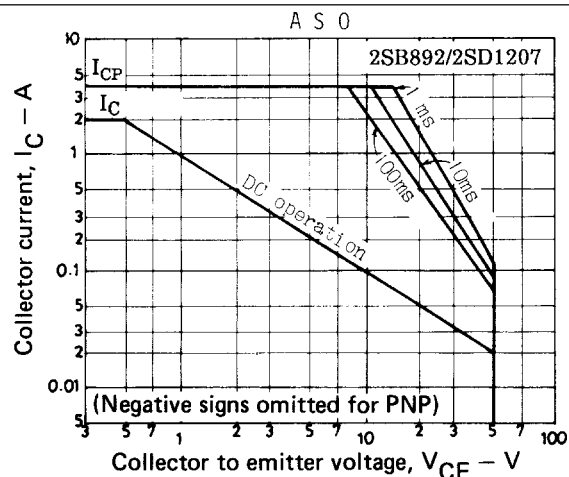
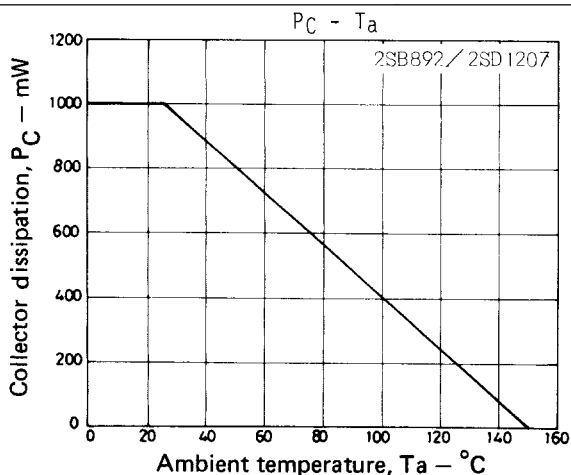
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)1A, I_B=(-)50mA$		0.15	0.4	V
				(-0.3)	(-0.7)	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=(-)1A, I_B=(-)50mA$		(-0.9)	(-1.2)	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu A, I_E=0$	(-60)			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)1mA, R_{BE}=\infty$	(-50)			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=(-)10\mu A, I_C=0$	(-6)			V





2SB892/2SD1207



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